

December 1994

LM760 High Speed Differential Comparator

General Description

The LM760 is a differential voltage comparator offering considerable speed improvement over the LM710 family and operates from symmetric supplies of $\pm 4.5V$ to $\pm 6.5V$. The LM760 can be used in high speed analog-to-digital conversion systems and as a zero crossing detector in disc file and tape amplifiers. The LM760 output features balanced rise and fall times for minimum skew and close matching between the complementary outputs. The outputs are TTL compatible with a minimum sink capability of two gate loads.

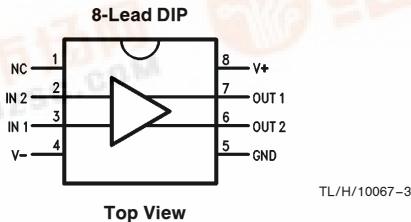
Features

- Guaranteed high speed— 25 ns response time
- Guaranteed delay matching on both outputs
- Complementary TTL compatible outputs
- High sensitivity
- Standard supply voltages

Applications

- High speed A-to-D
- Peak or zero detector

Connection Diagram



Ordering Information

Temperature Range Commercial 0°C to $+70^{\circ}\text{C}$	Package Type	NSC Package Drawing
LM760CN	8-lead Plastic DIP	N08E

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Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature Range		Positive Supply Voltage	+ 8.0V
Metal Can and Ceramic DIP	–65°C to + 175°C	Negative Supply Voltage	–8.0V
Molded DIP	–65°C to + 150°C	Peak Output Current	10 mA
		Differential Input Voltage	± 5.0V
Operating Temperature Range		Input Voltage	$V^+ \geq V_I \geq V^-$
Military (LM760)	–55°C to + 125°C	ESD Susceptibility	TBD
Commercial (LM760C)	0°C to + 70°C		
Lead Temperature			
Metal Can and Ceramic DIP (Soldering, 60 sec.)	300°C		
Molded DIP (Soldering, 10 sec.)	265°C		

LM760

Electrical Characteristics

$V_{CC} = \pm 4.5V$ to $\pm 6.5V$, $T_A = -55^\circ C$ to $+125^\circ C$, $T_A = 25^\circ C$ for typical figures, unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IO}	Input Offset Voltage	$R_S \leq 200\Omega$		1.0	6.0	mV
I_{IO}	Input Offset Current			0.5	7.5	μA
I_{IB}	Input Bias Current			8.0	60	μA
R_O	Output Resistance (Either Output)	$V_O = V_{OH}$		100		Ω
t_{PD}	Response Time	$T_A = 25^\circ C$ (Note 3)		18	30	ns
		$T_A = 25^\circ C$ (Note 4)			25	
		(Note 5)		16		
Δt_{PD}	Response Time Difference between Outputs (Note 1) $(t_{PD} \text{ of } +V_{I1}) - (t_{PD} \text{ of } -V_{I2})$	$T_A = 25^\circ C$			5.0	ns
	$(t_{PD} \text{ of } +V_{I2}) - (t_{PD} \text{ of } -V_{I1})$	$T_A = 25^\circ C$			5.0	
	$(t_{PD} \text{ of } +V_{I1}) - (t_{PD} \text{ of } +V_{I2})$	$T_A = 25^\circ C$			7.5	
	$(t_{PD} \text{ of } -V_{I1}) - (t_{PD} \text{ of } -V_{I2})$	$T_A = 25^\circ C$			7.5	
R_I	Input Resistance	$f = 1.0 \text{ MHz}$		12		$k\Omega$
C_I	Input Capacitance	$f = 1.0 \text{ MHz}$		8.0		pF
$\Delta V_{IO}/\Delta T$	Average Temperature Coefficient of Input Offset Voltage	$R_S = 50\Omega$, $T_A = -55^\circ C$ to $+125^\circ C$		3.0		$\mu V/^\circ C$
$\Delta I_{IO}/\Delta T$	Average Temperature Coefficient of Input Offset Current	$T_A = +25^\circ C$ to $+125^\circ C$		2.0		$nA/^\circ C$
		$T_A = +25^\circ C$ to $-55^\circ C$		7.0		
V_{IR}	Input Voltage Range	$V_{CC} = \pm 6.5V$	± 4.0	± 4.5		V
V_{IDR}	Differential Input Voltage Range			± 5.0		V
V_{OH}	Output Voltage HIGH (Either Output)	$0 \text{ mA} \leq I_{OH} \leq 5.0 \text{ mA}$ $V_{CC} = \pm 5.0V$	2.4	3.2		V
		$I_{OH} = 80 \mu A$, $V_{CC} = \pm 4.5V$	2.4	3.0		
V_{OL}	Output Voltage LOW (Either Output)	$I_{OL} = 3.2 \text{ mA}$		0.25	0.4	V
I^+	Positive Supply Current	$V_{CC} = \pm 6.5V$		18	32	mA
I^-	Negative Supply Current	$V_{CC} = \pm 6.5V$		9.0	16	mA

LM760C

Electrical Characteristics

$V_{CC} = \pm 4.5V$ to $\pm 6.5V$, $T_A = 0^\circ C$ to $+70^\circ C$, $T_A = 25^\circ C$ for typical figures, unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IO}	Input Offset Voltage	$R_S \leq 200\Omega$		1.0	6.0	mV
I_{IO}	Input Offset Current			0.5	7.5	μA
I_{IB}	Input Bias Current			8.0	60	μA
R_O	Output Resistance (Either Output)	$V_O = V_{OH}$		100		Ω
t_{PD}	Response Time	$T_A = 25^\circ C$ (Note 3)		18	30	ns
		$T_A = 25^\circ C$ (Note 4)			25	
		(Note 5)			16	
Δt_{PD}	Response Time Difference between Outputs (Note 1) $(t_{PD} \text{ of } +V_{I1}) - (t_{PD} \text{ of } -V_{I2})$	$T_A = 25^\circ C$			5.0	ns
	$(t_{PD} \text{ of } +V_{I2}) - (t_{PD} \text{ of } -V_{I1})$	$T_A = 25^\circ C$			5.0	
	$(t_{PD} \text{ of } +V_{I1}) - (t_{PD} \text{ of } +V_{I2})$	$T_A = 25^\circ C$			10	
	$(t_{PD} \text{ of } -V_{I1}) - (t_{PD} \text{ of } -V_{I2})$	$T_A = 25^\circ C$			10	
R_I	Input Resistance	$f = 1.0 \text{ MHz}$		12		$k\Omega$
C_I	Input Capacitance	$f = 1.0 \text{ MHz}$		8.0		pF
$\Delta V_{IO}/\Delta T$	Average Temperature Coefficient of Input Offset Voltage	$R_S = 50\Omega$, $T_A = 0^\circ C$ to $+70^\circ C$		3.0		$\mu V/\text{ }^\circ C$
$\Delta I_{IO}/\Delta T$	Average Temperature Coefficient of Input Offset Current	$T_A = +25^\circ C$ to $+70^\circ C$		5.0		$nA/\text{ }^\circ C$
		$T_A = +25^\circ C$ to $0^\circ C$		10		
V_{IR}	Input Voltage Range	$V_{CC} = \pm 6.5V$	± 4.0	± 4.5		V
V_{IDR}	Differential Input Voltage Range			± 5.0		V
V_{OH}	Output Voltage HIGH (Either Output)	$0 \text{ mA} \leq I_{OH} \leq 5.0 \text{ mA}$ $V_{CC} = +5.0V$	2.4	3.2		V
		$I_{OH} = 80 \mu A$, $V_{CC} = \pm 4.5V$	2.5	3.0		
V_{OL}	Output Voltage LOW (Either Output)	$I_{OL} = 3.2 \text{ mA}$		0.25	0.4	V
I^+	Positive Supply Current	$V_{CC} = \pm 6.5V$		18	34	mA
I^-	Negative Supply Current	$V_{CC} = \pm 6.5V$		9.0	16	mA

Note 1: $T_J \text{ Max} = 150^\circ C$.

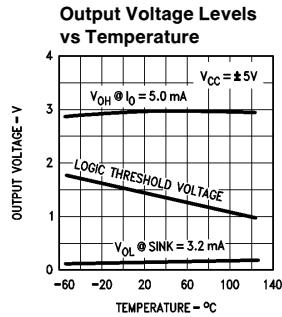
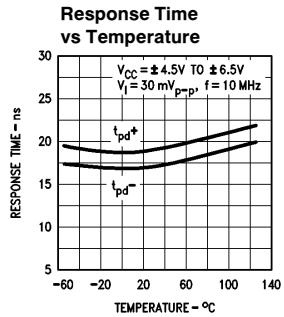
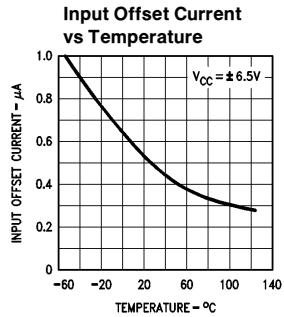
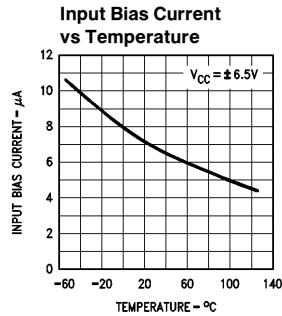
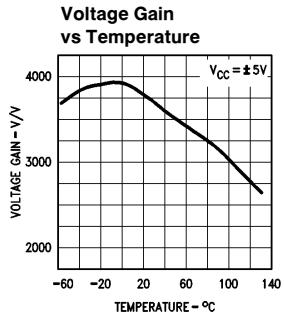
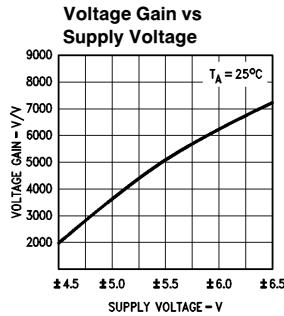
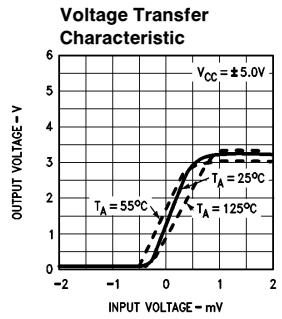
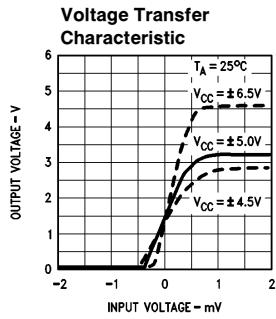
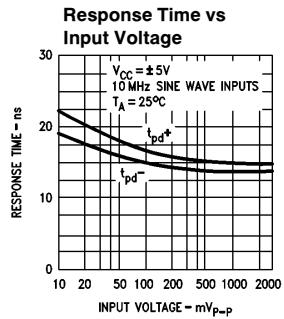
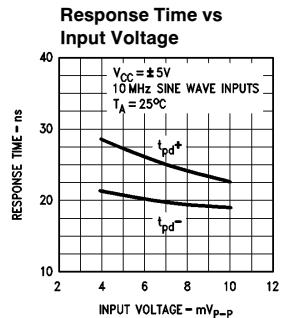
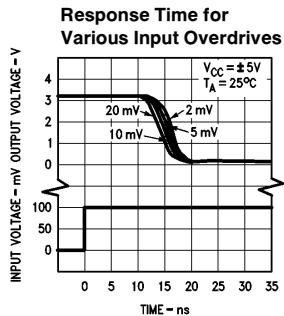
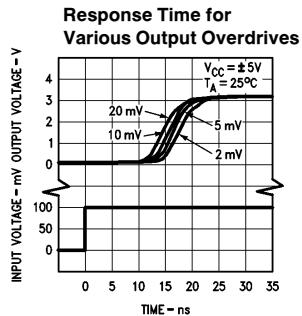
Note 2: Ratings apply to ambient temperature at $25^\circ C$.

Note 3: Response time measured from the 50% point of a 30 mV_{P-P} 10 MHz sinusoidal input to the 50% point of the output.

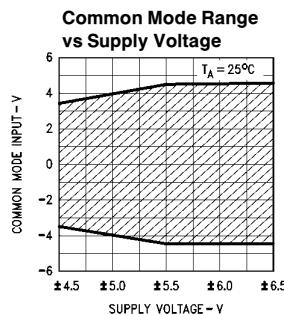
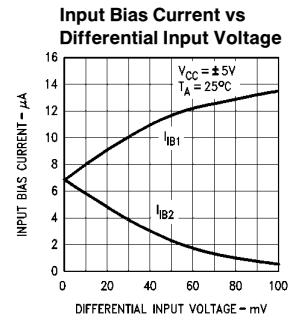
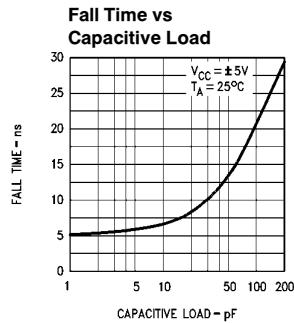
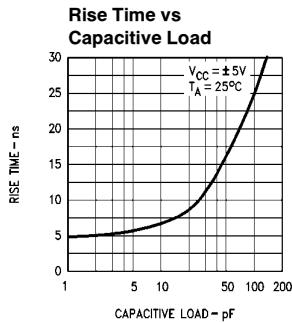
Note 4: Response time measured from the 50% point of a 2.0 V_{P-P} 10 MHz sinusoidal input to the 50% point of the output.

Note 5: Response time measured from the start of a 100 mV input step with 5.0 mV overdrive to the time when the output crosses the logic threshold.

Typical Performance Characteristics

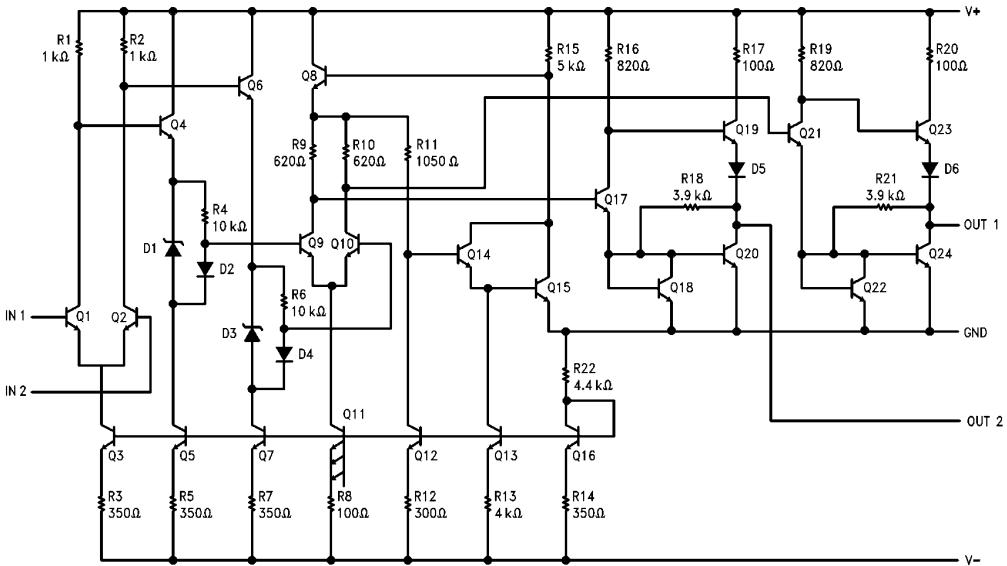


Typical Performance Characteristics (Continued)



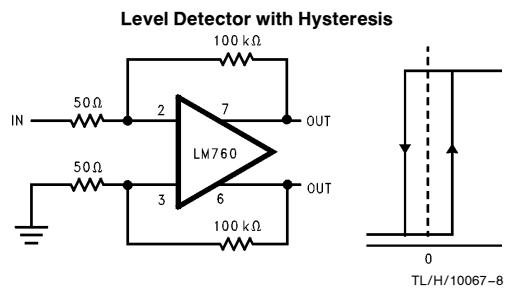
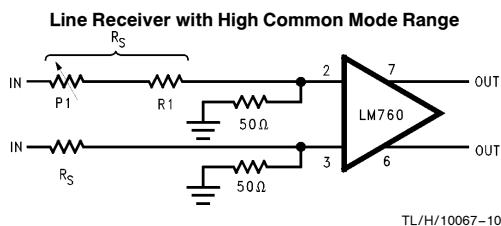
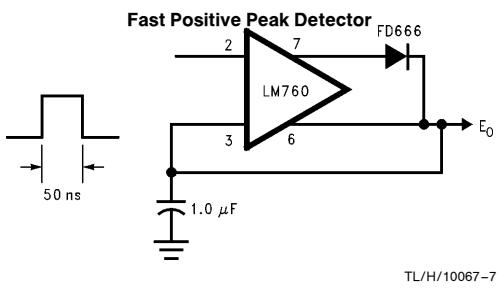
TL/H/10067-6

Equivalent Circuit

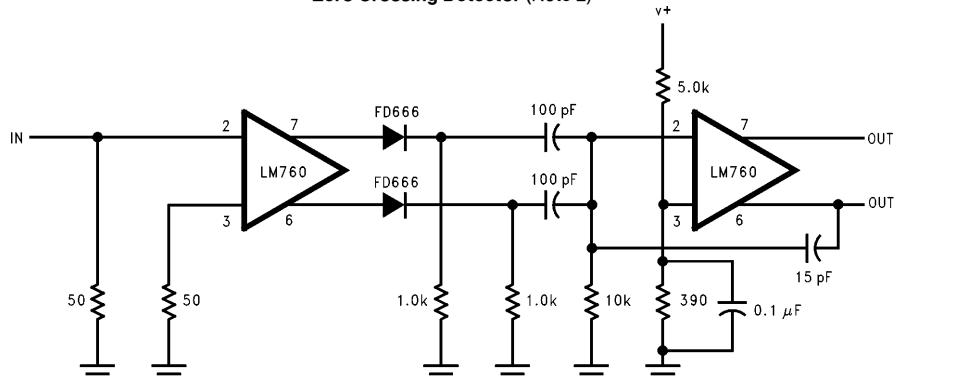


TL/H/10067-4

Typical Applications (Note 1)



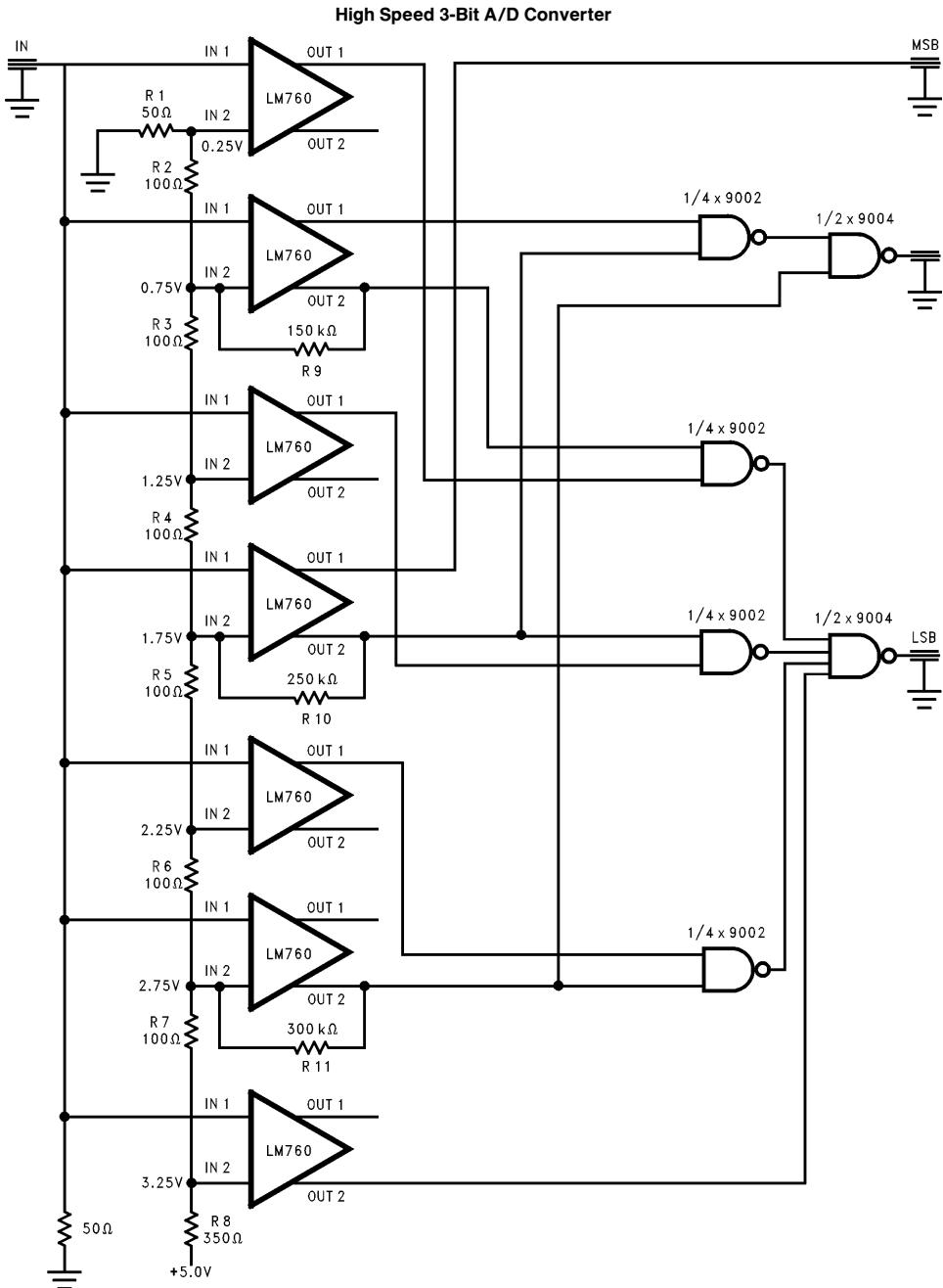
Zero Crossing Detector (Note 2)



Note 1: Lead numbers shown are for Metal Package only.

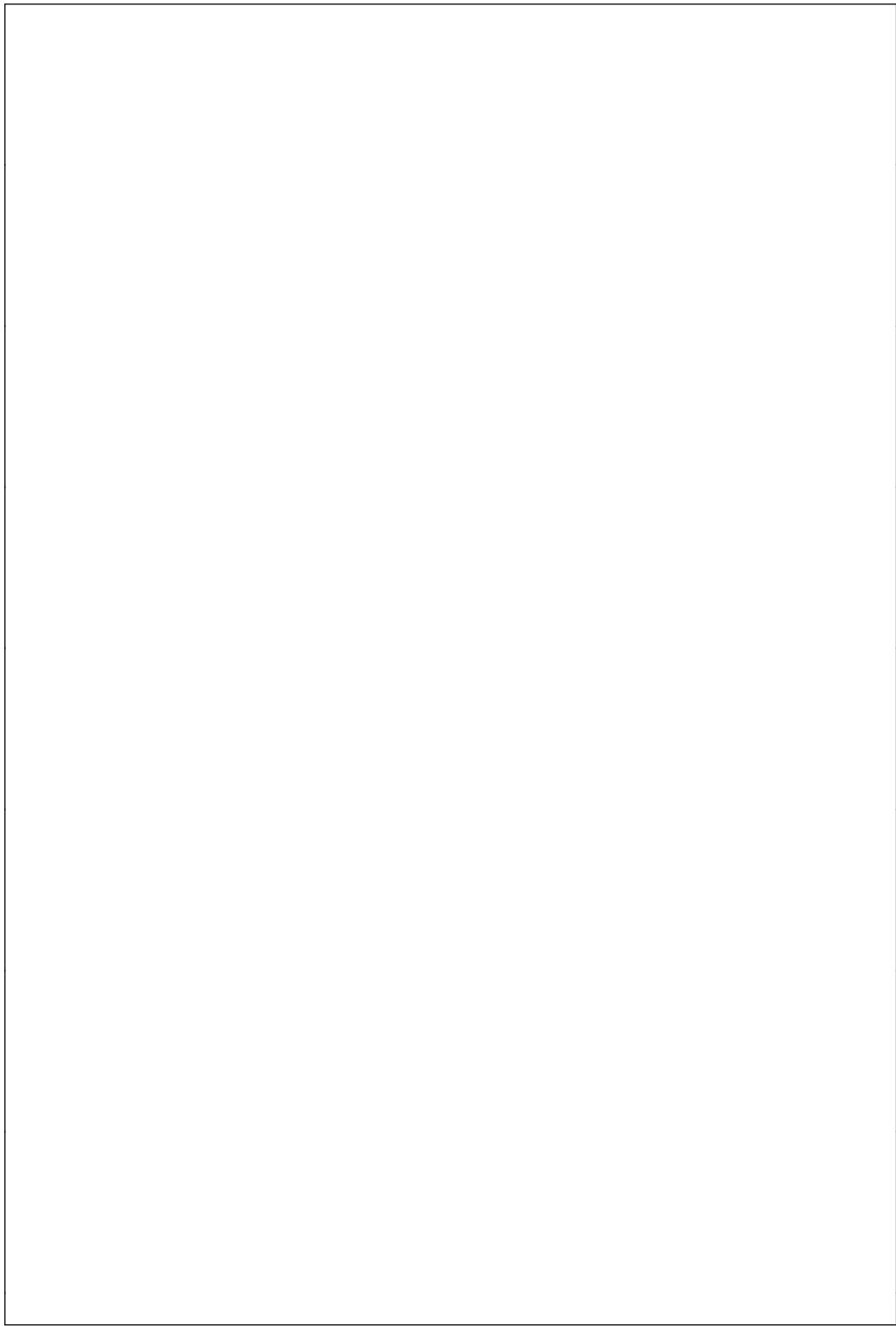
Note 2: All resistor values in ohms.

Typical Applications (Note 1) (Continued)

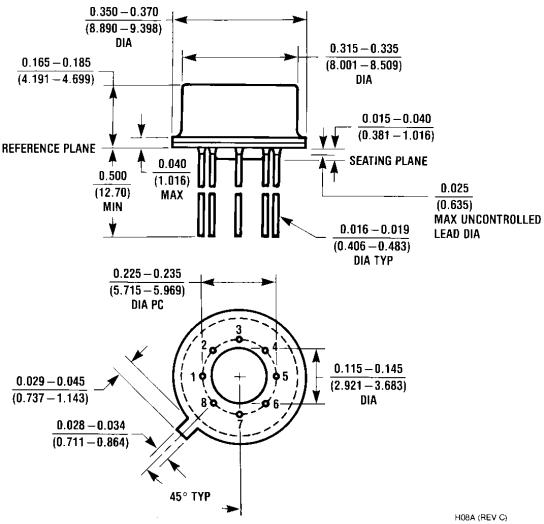


Input voltage range = 3.5V
Typical conversion speed = 30 ns

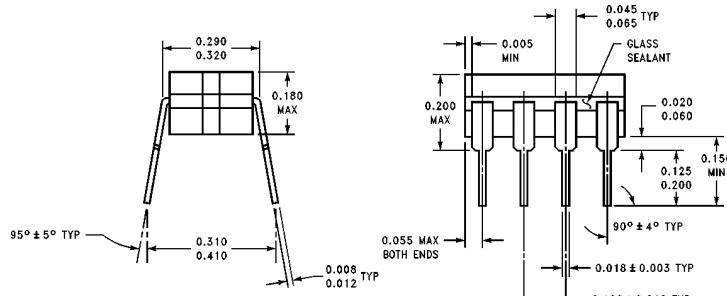
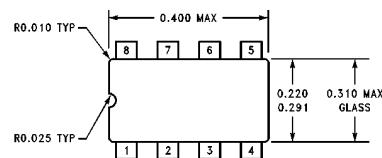
TL/H/10067-11



Physical Dimensions inches (millimeters)



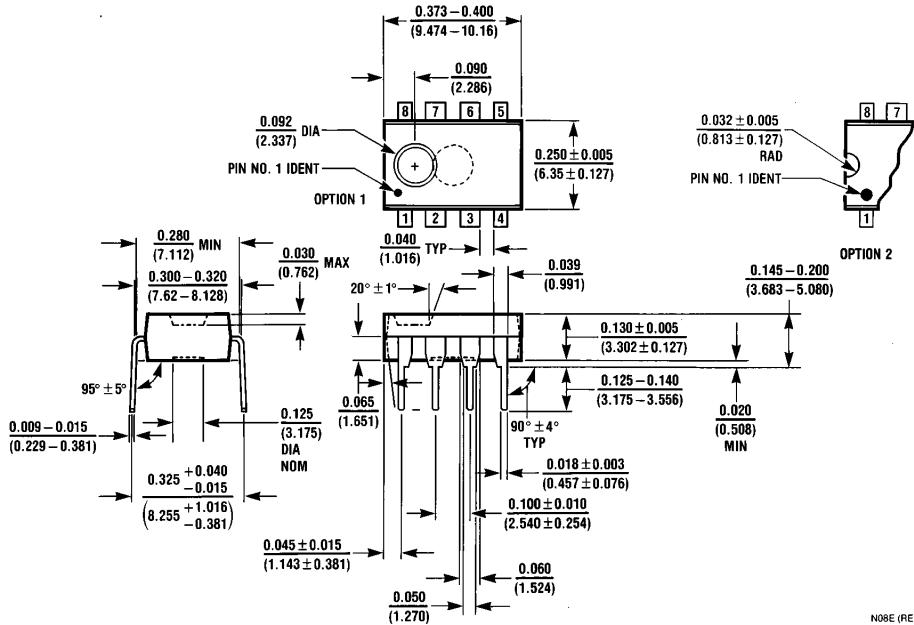
8-Lead Metal Can Package (H)
Order Number LM760CH or LM760H
NS Package Number H08A



8-Lead Ceramic Dual-In-Line Package (J)
Order Number LM760CJ or LM760J
NS Package Number J08A

LM760 High Speed Differential Comparator

Physical Dimensions inches (millimeters) (Continued)



8-Pin Molded Dual-In-Line Package (N)

Order Number LM760CN

NS Package Number N08E

LIFE SUPPORT POLICY

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National Semiconductor Corporation
1111 West Bardin Road
Arlington, TX 76017
Tel: (1800) 272-9959
Fax: (1800) 737-7018

National Semiconductor Europe
Fax: (+49) 0-180-530 85 86
Email: cnjwge@tevm2.nsc.com
Deutsch Tel: (+49) 0-180-530 85 85
English Tel: (+49) 0-180-532 78 32
Français Tel: (+49) 0-180-532 93 58
Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
13th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
Tel: 81-043-299-2309
Fax: 81-043-299-2408